MBR2535CTG, MBR2545CTG

Switch-mode Power Rectifiers

The MBR2535CTG/45CTG series uses the Schottky Barrier principle with a platinum barrier metal. These state-of-the-art devices have the following features:

Features

- Guardring for Stress Protection
- Low Forward Voltage
- 175°C Operating Junction Temperature
- These are Pb-Free Devices*

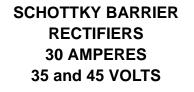
Mechanical Characteristics

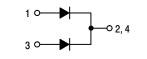
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

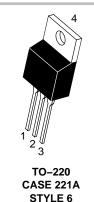


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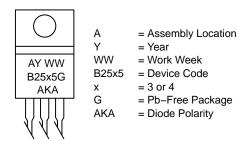
http://onsemi.com







MARKING DIAGRAM



ORDERING INFORMATION

Device	Package	Shipping
MBR2535CTG	TO-220 (Pb-Free)	50 Units/Rail
MBR2545CTG	TO-220 (Pb-Free)	50 Units/Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MBR2535CTG, MBR2545CTG

MAXIMUM RATINGS

Rating	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage MBR2535CTG MBR2545CTG	V _{RRM} V _{RWM} V _R	35 45	V	
Average Rectified Forward Current (Rated V_R , $T_C = 160^{\circ}C$) Per Device Per Diode	I _{F(AV)}	30 15	A	
Peak Repetitive Forward Current per Diode Leg (Rated V_R , Square Wave, 20 kHz, $T_C = 150^{\circ}C$)	I _{FRM}	30	А	
Non-Repetitive Peak Surge Current per Diode Leg (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	I _{FSM}	150	А	
Peak Repetitive Reverse Surge Current (2.0 µs, 1.0 kHz)	I _{RRM}	1.0	А	
Storage Temperature Range	T _{stg}	-65 to +175	°C	
Operating Junction Temperature (Note 1)	TJ	-65 to +175	°C	
Voltage Rate of Change (Rated V _R)	dv/dt	10,000	V/μs	
ESD Ratings: Machine Model = C Human Body Model = 3B	ESD	> 400 > 8000	V	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS (Per Leg)

Characteristic	Symbol	Value	Unit		
Thermal Resistance, Junction-to-Case Junction-to-Ambient (Note 2)	${\sf R}_{ heta {\sf JC}} \ {\sf R}_{ heta {\sf JA}}$	1.5 50	°C/W		

2. When mounted using minimum recommended pad size on FR-4 board.

ELECTRICAL CHARACTERISTICS (Per Diode)

Symbol	Characteristic	Condition	Min	Тур	Мах	Unit
VF	Instantaneous Forward Voltage (Note 3)	$ I_{F} = 15 \text{ Amp, } T_{J} = 25^{\circ}\text{C} $ $ I_{F} = 15 \text{ Amp, } T_{J} = 125^{\circ}\text{C} $ $ I_{F} = 30 \text{ Amp, } T_{J} = 25^{\circ}\text{C} $ $ I_{F} = 30 \text{ Amp, } T_{J} = 125^{\circ}\text{C} $	- - -	_ 0.50 _ 0.65	0.62 0.57 0.82 0.72	V
۱ _R	Instantaneous Reverse Current (Note 3)	Rated dc Voltage, $T_J = 25^{\circ}C$ Rated dc Voltage, $T_J = 125^{\circ}C$	-	_ 9.0	0.2 25	mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse Test: Pulse Width = $300 \ \mu$ s, Duty Cycle $\le 2.0\%$.

MBR2535CTG, MBR2545CTG

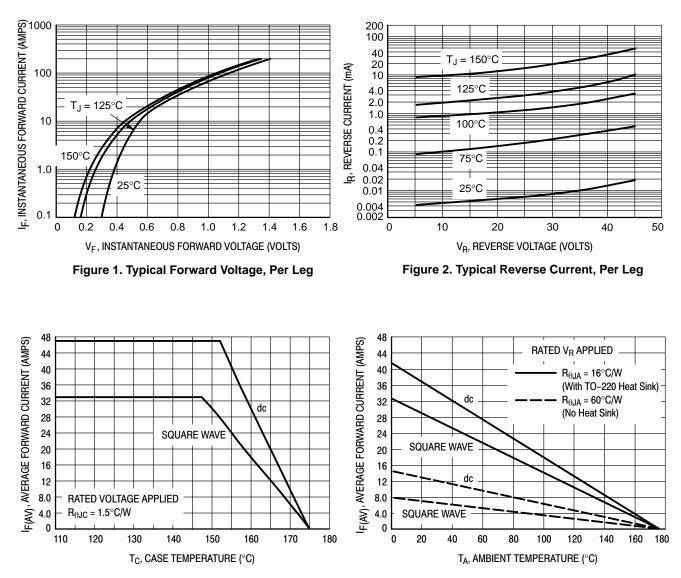


Figure 3. Current Derating, Per Device

Figure 4. Current Derating, Per Device

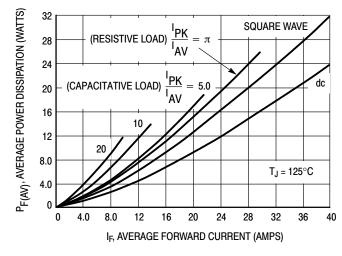


Figure 5. Forward Power Dissipation

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		TO-220 CASE 221A ISSUE AK						DATE	13 JAN 2022
SCALE 1:1			1. C 2. C 3. C	CONTR DIMEN LEAD	ROLLING DI ISION Z DEI D IRREGULA	MENSION FINES A ZO ARITIES AR	ONE WHERE AL E ALLOWED.		
			4. N	лах м	VIDTHFOR	F102 DEV	ICE = 1.35MM		
			Г		INC	HES	MILLIM	ETERS	
				ым 🛛	MIN.	MAX.	MIN.	MAX.	
	2 3			A	0.570	0.620	14.48	15.75	
				в	0.380	0.415	9.66	10.53	
н —	₩₩			с	0.160	0.190	4.07	4.83	
	7 \7	H I		D	0.025	0.038	0.64	0.96	
z_				F	0.142	0.161	3.60	4.09	
<u> </u>	I K			G	0.095	0.105	2.42	2.66	
				н	0.110	0.161	2.80	4.10	
	Щ Щ <u> </u>	Ü I		J	0.014	0.024	0.36	0.61	
	Г <mark>і</mark>			к	0.500	0.562	12.70	14.27	
V — + I I-	►- ``.			L	0.045	0.060	1.15	1.52	
G 	. <mark> </mark> ^{J−}			N	0.190	0.210	4.83	5.33	
· · · ·	- → D			Q	0.100	0.120	2.54	3.04	
	N 🖛			R	0.080	0.110	2.04	2.79	
				s	0.045	0.055	1.15	1.41	
				т	0.235	0.255	5.97	6.47	
				U	0.000	0.050	0.00	1.27	
				V	0.045		1.15		
				Z		0.080		2.04	
2. 3. 4. STYLE 5: PIN 1. 2.	BASE PIN 1. COLLECTOR 2. EMITTER 3. COLLECTOR 4. STYLE 6: GATE DRAIN 2.	EMITTER COLLECTOR EMITTER ANODE CATHODE	IN 1. CAT 2. ANO 3. GAT 4. ANO LE 7: IN 1. CAT 2. ANO	ode Te ode Thode ode		2. 3. 4. STYLE 8: PIN 1. 2.	MAIN TERMINAL MAIN TERMINAL GATE MAIN TERMINAL CATHODE ANODE	2	
4. STYLE 9: PIN 1.	DRAIN 4. STYLE 10 GATE PIN 1.	ANODE CATHODE GATE P SOURCE	3. CAT 4. ANO LE 11: IN 1. DR/ 2. SOU	ode Ain		4. STYLE 12: PIN 1.	EXTERNAL TRIP ANODE MAIN TERMINAL MAIN TERMINAL	. 1	
3.	EMITTER 3.	DRAIN SOURCE	3. GAT 4. SOL	ΤE		3.	GATE NOT CONNECTI		

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